

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer.

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



DISCRETE SEMICONDUCTORS

DATA SHEET

BT152B seriesThyristors

Product specification

September 1997



Thyristors BT152B series

GENERAL DESCRIPTION

Glass passivated thyristors in a plastic envelope suitable for surface mounting, intended for use in applications high requiring bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

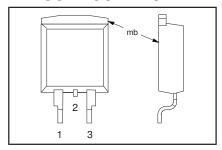
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
.,	BT152B-	400R	600R	800R	,,
V_{DRM}	Repetitive peak off-state	450	650	800	V
V _{RRM} I _{T(AV)}	voltages Average on-state current	13	13	13	Α
I _{T(RMS)}	RMS on-state current	20	20	20	A
I _{TSM}	Non-repetitive peak on-state current	200	200	200	A

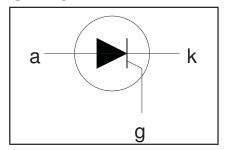
PINNING - SOT404

PIN	DESCRIPTION			
1	cathode			
2	anode			
3	gate			
mb	anode			

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V_{DRM}	Repetitive peak off-state voltages		-	-400R 450 ¹	-600R 650 ¹	-800R 800	V
I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 103$ °C all conduction angles half sine wave; $T_j = 25$ °C prior to surge	- -		13 20		A A
.2.		t = 10 ms t = 8.3 ms	- -		200 220		A A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after triggering	t = 10 ms $I_{TM} = 50 \text{ A}; I_{G} = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-		200 200		A²s A/μs
$V_{\rm GM}$	Peak gate current Peak gate voltage		- -		5 5		A V
V _{RGM} P _{GM}	Peak reverse gate voltage Peak gate power Average gate power	over any 20 ms period	- - -		5 20 0.5		W W W
$ \begin{array}{c} P_{G(AV)}^{GM} \\ T_{stg} \\ T_{j} \end{array} $	Storage temperature Operating junction temperature	ovor any 20 mo ponou	-40 -		150 125		O, O

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

Thyristors BT152B series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance		-	-	1.1	K/W
R _{th j-a}	junction to mounting base Thermal resistance junction to ambient	minimum footprint, FR4 board	-	55	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	3	32	mA
l I _L	Latching current	$V_D^2 = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	25	80	mA
l I _H	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	15	60	mA
ĺΫ́Τ	On-state voltage	$I_T = 40 \text{ A}$	-	1.4	1.75	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$; $I_T = 0.1 A$; $T_j = 125 °C$	0.25	0.4	-	V
$ I_{D},I_{R} $	Off-state leakage current	$V_D = V_{DRM(max)}^{Stationary}; V_R = V_{RRM(max)}; T_i = 125 °C$	-	0.2	1.0	mΑ

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential waveform gate open circuit	200	300	-	V/μs
t _{gt}	Gate controlled turn-on	$V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ Å}$; $dI_G/dt = 5 \text{ A/}\mu\text{s}$; $I_{TM} = 40 \text{ Å}$	-	2	-	μs
t _q	Circuit commutated turn-off time	$\begin{array}{l} V_{D}^{\text{IW}} = 67\% \ V_{\text{DRM(max)}}; \ T_{j} = 125 \ ^{\circ}\text{C}; \\ I_{TM} = 50 \ A; \ V_{R} = 25 \ V; \ dI_{TM}/dt = 30 \ A/\mu s; \\ dV_{D}/dt = 50 \ V/\mu s; \ R_{GK} = 100 \ \Omega \end{array}$	-	70	-	μs

Thyristors BT152B series

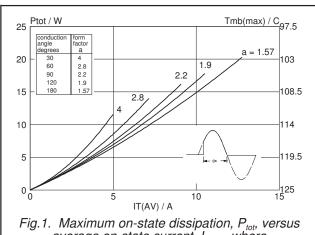


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$.

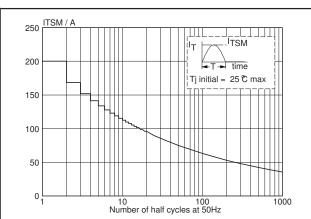


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

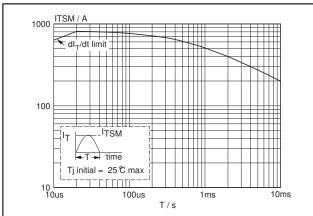


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

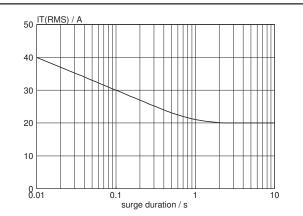


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 103 \,^{\circ}\text{C}$.

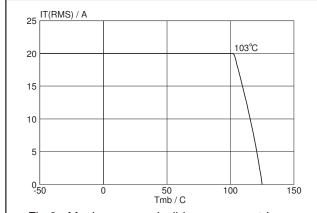
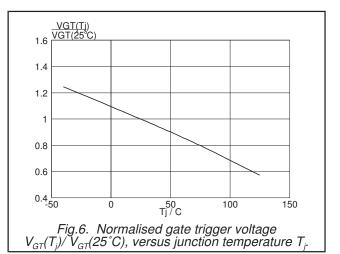
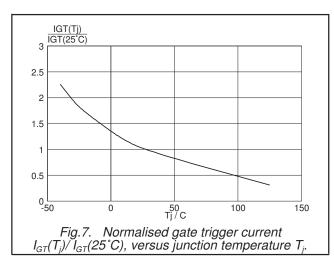
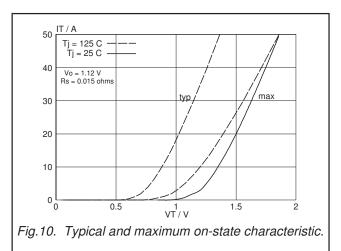


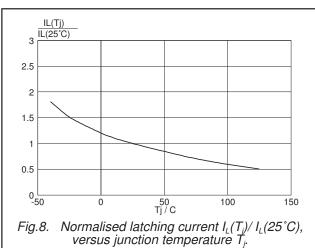
Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

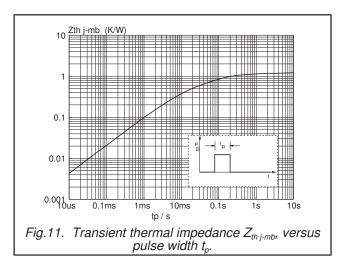


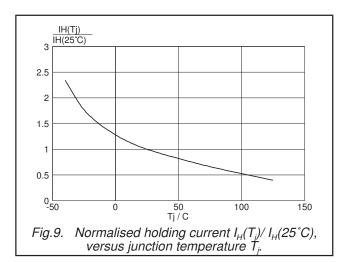
Thyristors BT152B series

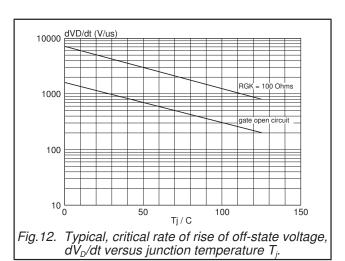






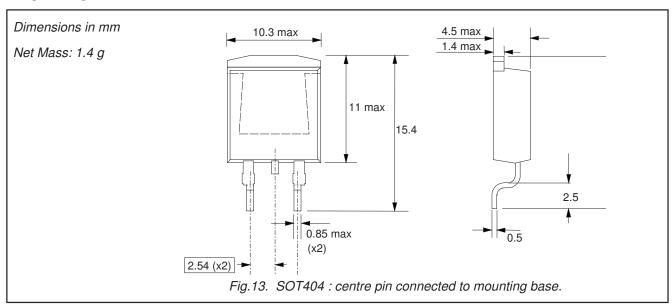






Thyristors BT152B series

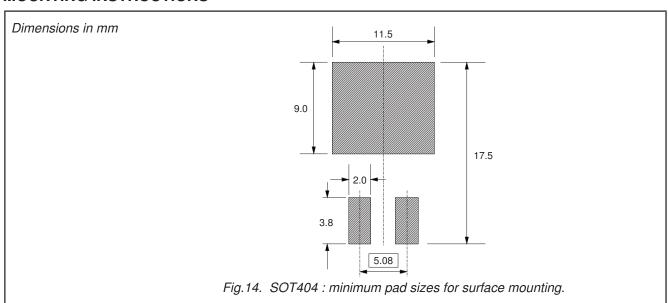
MECHANICAL DATA



Notes

1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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